



Silicon Schottky Barrier Diode for Various Detector, High Speed Switching

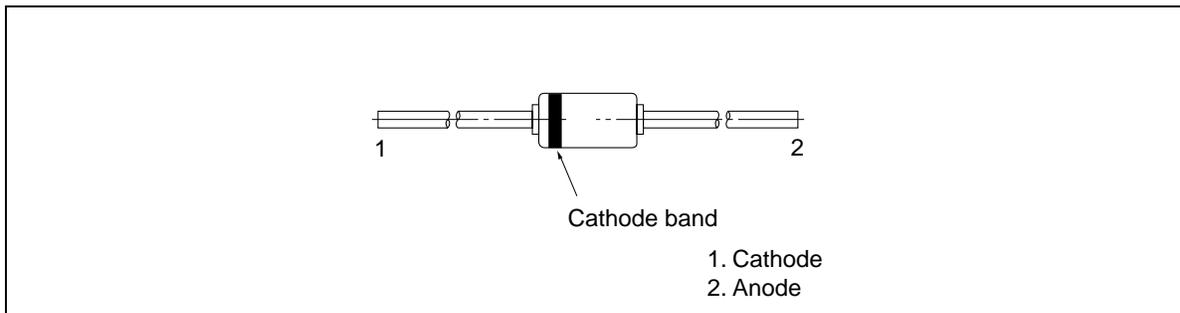
Features

- Detection efficiency is very good.
- Small temperature coefficient.
- High reliability with glass seal..

Ordering Information

Type No.	Cathode band	Mark	Package Code
1SS106	Black	Cathode band	DO-35

Pin Arrangement



Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_o	30	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Electrical Characteristics

($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward current	I_F	4.5	—		mA	$V_F = 1\text{ V}$
Reverse current	I_R	—	—	70	μA	$V_R = 6\text{ V}$
Capacitance	C	—	—	2.0	pF	$V_R = 1\text{ V}$, $f = 1\text{ MHz}$
ESD-Capability **1	—	100	—	—	V	$C = 200\text{ pF}$, Both forward and reverse direction 1 pulse.

Note: 1. Failure criterion; $I_R \geq 140\ \mu\text{A}$ at $V_R = 6\text{ V}$